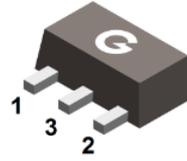
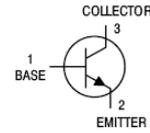


Features

- Epitaxial planar die construction
- Complimentary to PXT2907A
- High current
- Low voltage

HF



SOT-89

Mechanical Data

- Case: SOT-89
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
PXT2222A	SOT-89	1000 pcs / Tape & Reel	1P

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Breakdown Voltage	V _{CBO}	75	V
Collector-Emitter Breakdown Voltage	V _{CEO}	40	V
Emitter-Base Breakdown Voltage	V _{EBO}	6	V
Continuous Collector Current	I _C	0.6	A
Peak Collector Current	I _{CM}	0.8	A
Continuous Base Current	I _B	0.15	A
Peak Base Current	I _{BM}	0.2	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation	P _D	1.25	W
Thermal Resistance (Junction-to-Ambient) *1	R _{θJA}	100	°C/W
Thermal Resistance (Junction-to-Case) *1	R _{θJC}	45	°C/W
Thermal Resistance (Junction-to-Lead) *1	R _{θJL}	10	°C/W
Ambient Temperature	T _A	-55 ~ +150	°C
Operating junction Temperature	T _J	-65 ~ +150	°C
Storage Temperature Range	T _{STG}	-65 ~ +150	°C

Note 1: The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper

Electrical Characteristics (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	V _{(BR)CBO}	I _C = 10μA, I _E = 0	75	-	-	V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C = 10mA, I _B = 0	40	-	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E = 10μA, I _C = 0	6	-	-	V
Collector Cut-off Current	I _{CBO}	V _{CB} = 60V, I _E = 0	-	-	10	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 5V, I _C = 0	-	-	10	nA
DC Current Gain	h _{FE}	V _{CE} = 10V, I _C = 0.1mA	35	-	-	-
		V _{CE} = 10V, I _C = 1mA	50	-	-	-
		V _{CE} = 10V, I _C = 10mA	75	-	-	-
		V _{CE} = 10V, I _C = 150mA	100	-	300	-
		V _{CE} = 10V, I _C = 500mA	40	-	-	-
		V _{CE} = 1V, I _C = 150mA	50	-	-	-
Collector-emitter Saturation Voltage	V _{CE(sat)}	I _C = 500mA, I _B = 50mA	-	-	1	V
		I _C = 150mA, I _B = 15mA	-	-	0.3	V
Base-emitter Saturation Voltage	V _{BE(sat)}	I _C = 500mA, I _B = 50mA	-	-	2	V
		I _C = 150mA, I _B = 15mA	-	-	1.2	V
Base-Emitter Voltage	V _{BE(on)}	I _C = 200mA, V _{CE} = 10V	-	-	1	V
Transition Frequency	f _T	I _C = 20mA, V _{CE} = 10V f = 100MHz	300	-	-	MHz
Collector Output Capacitance	C _{OBO}	V _{CB} = 10V, I _E = 0, f = 1MHz	-	-	8	pF
Noise Figure	N _F	V _{CE} = 10V, I _C = 100μA R _S = 1kΩ, f = 1.0kHz	-	-	4.0	dB
Delay Time	t _d	V _{CC} = 30V, I _C = 150mA V _{BE(OFF)} = -0.5V, I _{B1} = 15mA	-	-	10	ns
Rise Time	t _r		-	-	25	ns
Storage Time	t _s		-	-	225	ns
Fall Time	t _f		I _{B1} = -I _{B2} = 15mA	-	-	60

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

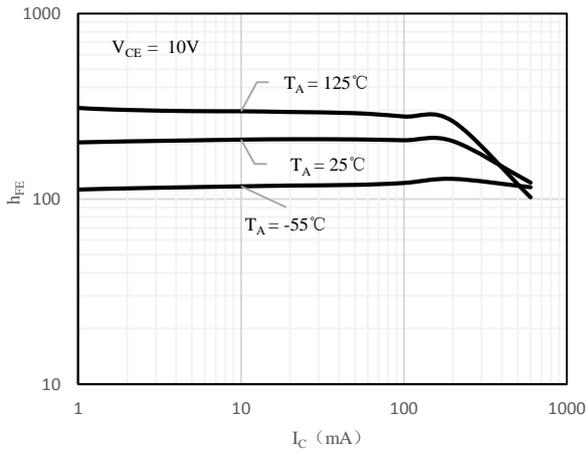


Fig 1 h_{FE} vs. I_C

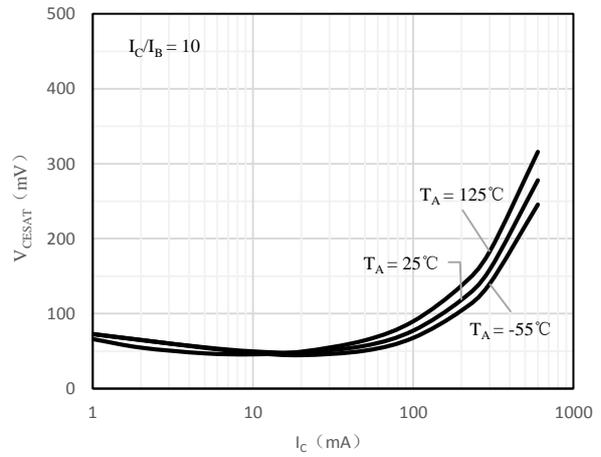


Fig 2 $V_{CE(sat)}$ vs. I_C

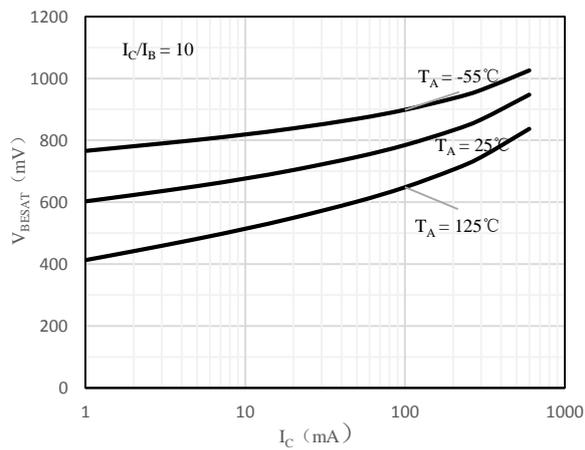


Fig 3 $V_{BE(sat)}$ vs. I_C

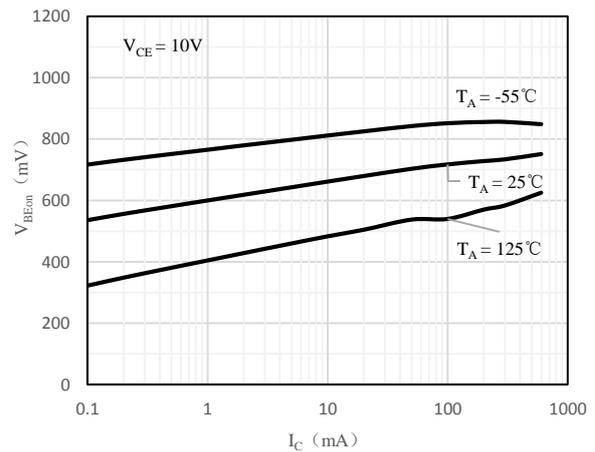


Fig 4 $V_{BE(ON)}$ vs. I_C

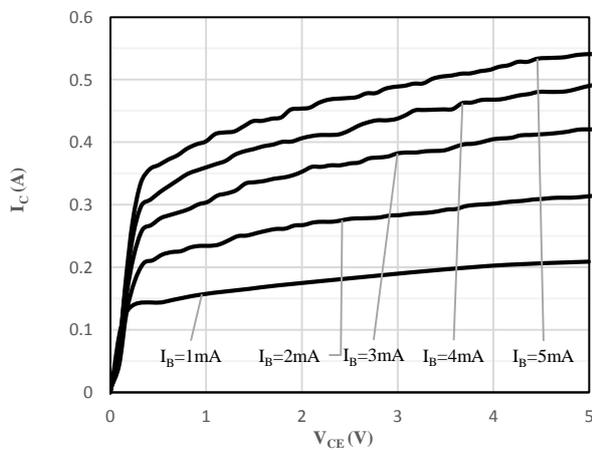


Fig 5 I_C vs. V_{CE}

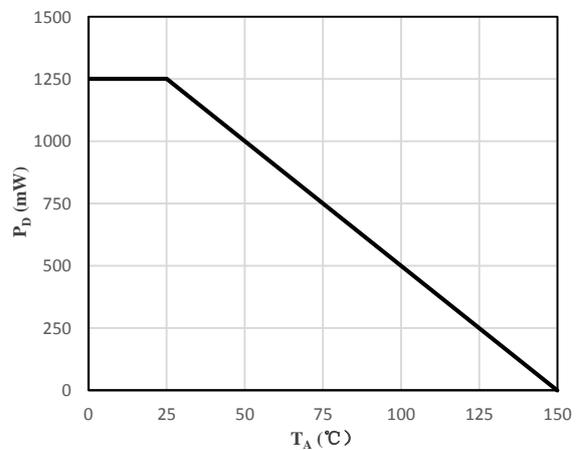


Fig 6 P_D vs. T_A

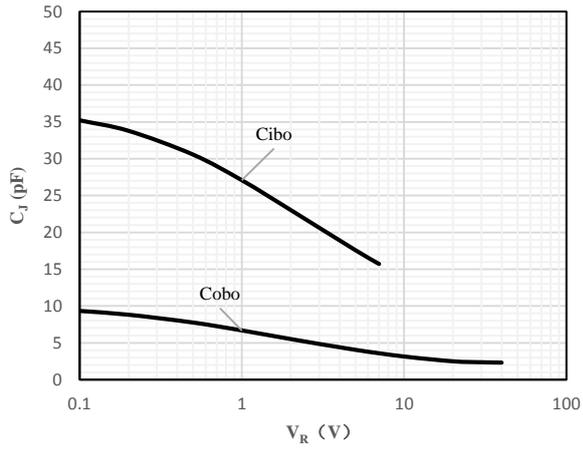
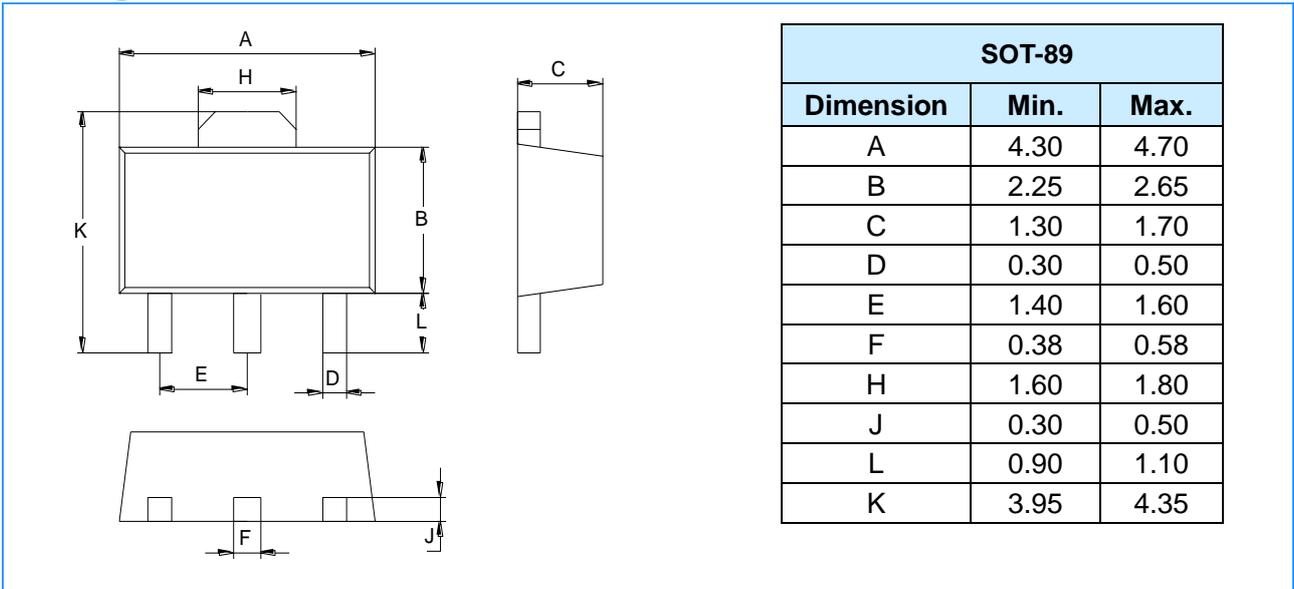
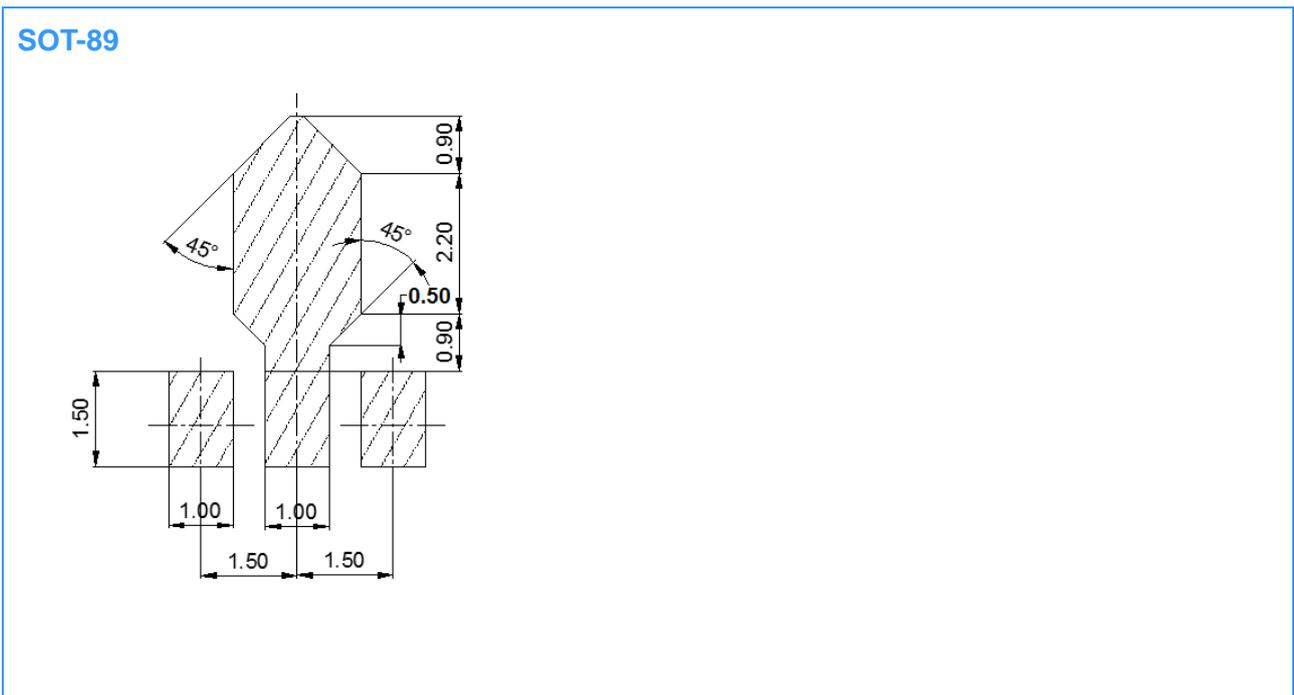


Fig 7 C_J vs. V_R

Package Outline Dimensions (Unit: mm)



Mounting Pad Layout (Unit: mm)



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